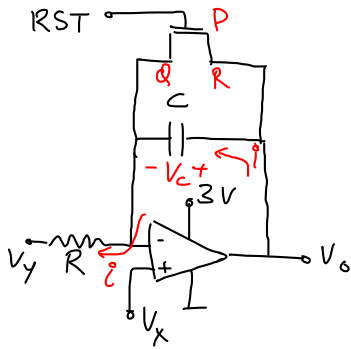


- \* ramp only occurs when RST is 0. While  $f_{RST} = 1 \text{ kHz}$ , the ramp exists for  $\sim 0.9 \text{ ms}$  (from counter output screen shot)



\* input goes  $0.25$  to  $2.75 \text{ V}$

$\Rightarrow$  ramp must cover this range.

lets go a bit wider to account for

component tolerances etc :  $0.2 \text{ V}$  to  $2.8 \text{ V}$

\* slope of ramp :  $(2.8 - 0.2) / 0.9 \text{ ms} = 2.9 \text{ V/ms}$

- \* with  $V_x$  fixed, for  $V_o$  to increase over time (slope  $> 0$ ), current must flow in indicated direction

$$* i = \frac{C dV_c}{dt} = C \frac{d}{dt}(V_o - V_x) = \underbrace{\frac{C dV_o}{dt}}_{\text{ramp slope}}$$

$$* i = \frac{V_x - V_y}{R}$$

\* @ RST,  $V_c = 0 \Rightarrow V_o = V_x$  (start of the ramp, chosen to be  $0.2 \text{ V}$ )

$$* \frac{C dV_o}{dt} = \frac{V_x - V_y}{R} \Rightarrow 2900 = \frac{V_x - V_y}{RC}$$

$$2900 = \frac{0.2 - V_y}{RC}$$

$\rightarrow V_y = 0$  is easy to make, we already have it @ opamp supply.

$$RC = 0.2 / 2900 = 68.97 \mu\text{s}$$

\* R dissipates  $\frac{(V_x - V_y)^2}{R} \Rightarrow$  use large R

\* breadboards have several pF parasitics, so choose  $C > 100 \text{ pF}$

\* ceramic capacitors more accurate than electrolytic which are typically used for high capacitances ( $\mu\text{F}$  & higher)

\* large C will take longer to discharge through FET resistance.

\* several RC combinations with these constraints will work!

\* my choice:  $V_x = 0.2 \text{ V}$ ,  $V_y = 0$ ,  $R = 6.8 \text{ k}\Omega$ ,  $C = 10 \text{ nF}$

\* for nFET,  $\odot$  clearly gate.

@ Reset,  $V3$  (the ramp  $= 2.8 \text{ V}$ )  $> V2 (= V_x = 0.2 \text{ V})$

$\therefore 3$  is drain &  $2$  is source